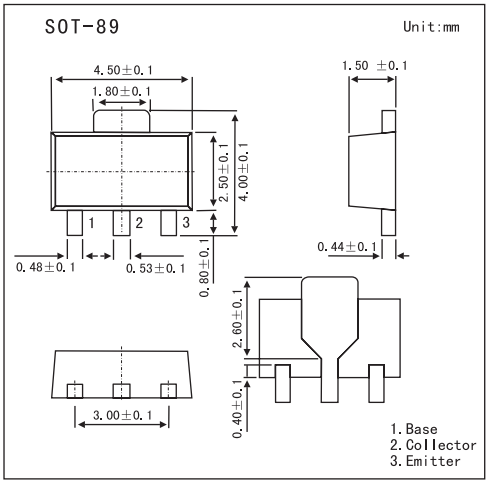
2SB1122



■ Features

- Adoption of FBET process..
- Very small size making it easy to provide highdensity hybrid ICs.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Collector current (pulse)	I_{CP}	-2	A
Collector dissipation	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

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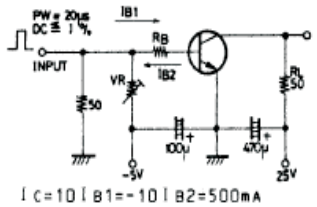
■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -50V , I_E = 0			-100	nA
Emitter cutoff current	I_{EBO}	V_{CB} = -4V , I_E = 0			-100	nA
DC current Gain	h_{FE}	V_{CE} = -2V , I_C = -100mA	100		560	
Gain bandwidth product	f_T	V_{CE} = -10V , I_C = -50mA		150		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , f = 1MHz		12		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -500mA , I_B = -50mA		-180	-500	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -500mA , I_B = -50mA		-0.9	-1.2	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = -10μA , I_C = 0	-5			V
Turn-on time	ton			40		ns
Storage time	tstg			300		ns
Fall time	tf			30		ns

IC=10IB1=-10IB2=500mA

■ h_{FE} Classification

Marking	BE			
Rank	R	S	T	U
hFE	100～200	140～280	200～400	280～560